

## Transistors

## 2.5V Drive Nch MOS FET

## RJK005N03

## ●Structure

Silicon N-channel MOS FET

## ●Features

- 1) Low On-resistance.
- 2) Low voltage drive (2.5V drive).

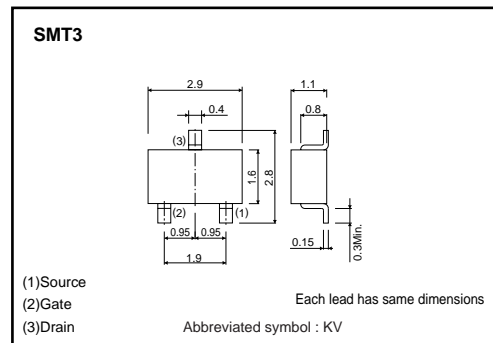
## ●Applications

Switching

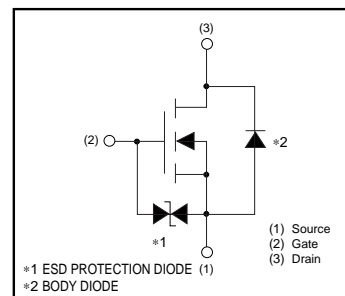
## ●Packaging specifications and hFE

Type	Package	Taping
	Code	T146
	Basic ordering unit (pieces)	3000
RJK005N03		○

## ●External dimensions (Unit : mm)



## ●Inner circuit



## ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DSS}$	30	V	
Gate-source voltage	$V_{GSS}$	$\pm 12$	V	
Drain current	Continuous	$I_D$	$\pm 500$	mA
	Pulsed	$I_{DP}$ *1	$\pm 2.0$	A
Source current (Body Diode)	Continuous	$I_S$	200	mA
	Pulsed	$I_{SP}$ *1	800	mA
Total power dissipation	$P_D$ *2	200	mW	
Channel temperature	$T_{ch}$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$ 

\*2 Each terminal mounted on a recommended land

## ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}$ *	625	°C/W

\* Each terminal mounted on a recommended land

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## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	±10	μA	$V_{GS}=\pm 12V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	–	–	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	1	μA	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.8	–	1.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	400	580	mΩ	$I_D=500mA, V_{GS}=4.5V$
		–	420	600	mΩ	$I_D=500mA, V_{GS}=4V$
		–	650	940	mΩ	$I_D=500mA, V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	0.5	–	–	S	$V_{DS}=10V, I_D=500mA$
Input capacitance	$C_{iss}$	–	60	–	pF	$V_{DS}=10V$
Output capacitance	$C_{oss}$	–	24	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	–	12	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	9	–	ns	$V_{DD}\doteq 15V$
Rise time	$t_r$ *	–	11	–	ns	$I_D=250mA$
Turn-off delay time	$t_{d(off)}$ *	–	16	–	ns	$V_{GS}=4V$
Fall time	$t_f$ *	–	31	–	ns	$R_L=60\Omega$
Total gate charge	$Q_g$ *	–	2.0	4.0	nC	$V_{DD}\doteq 24V$
Gate-source charge	$Q_{gs}$ *	–	0.6	–	nC	$V_{GS}=4V$
Gate-drain charge	$Q_{gd}$ *	–	0.7	–	nC	$I_D=500mA$

\*Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}$ *	–	–	1.2	V	$I_S=500mA, V_{GS}=0V$

\*Pulsed

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